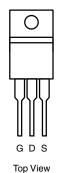


**Vishay Siliconix** 

## N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
	0.021 at V <sub>GS</sub> = 10 V	50 <sup>d</sup>			
100	0.023 at V <sub>GS</sub> = 8 V	49.7	30.2 nC		
	0.028 at V <sub>GS</sub> = 6 V	45			



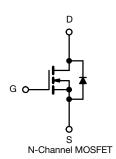
#### TO-220AB



- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>q</sub> and UIS Tested Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### **APPLICATIONS**

- DC/AC Inverters
- Primary Side Switching
- Synchronous Rectification



Ordering Information: SUP50N10-21P-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unless ot	herwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	100	N	
Gate-Source Voltage		V <sub>GS</sub>	± 20	- V	
Continuous Drain Current (T <sub>1</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	50 <sup>d</sup>	А	
Continuous Drain Current (1j = 150°C)	T <sub>C</sub> = 70 °C	'D	41.6		
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	60	A	
Avalanche Current	I <sub>AS</sub>	40			
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	80	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	Р	125 <sup>b</sup>	w	
	T <sub>A</sub> = 25 °C <sup>c</sup>	– P <sub>D</sub> –	3.1		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	1	0/00		

Notes:

a. Duty cycle  $\leq$  1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

d. Package limited.

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### Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS}$ = 0 V, I <sub>D</sub> = 250 µA	100			v
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2		4	v
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V$ , $V_{GS} = \pm 20 V$			± 250	nA
		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			50	
		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10$ V, $V_{GS} = 10$ V	20			А
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.017	0.021	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 8 V, I <sub>D</sub> = 9.6 A		0.019	0.023	Ω
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 8.7 A		0.022	0.028	
Forward Transconductancea	9 <sub>fs</sub>	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 10 A		40		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			2055		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 50 V, f = 1 MHz		227		
Reverse Transfer Capacitance	C <sub>rss</sub>			120		
Total Gate Charge <sup>c</sup>	Qg			45	68	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		10.5		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			15.9		
Gate Resistance	Rg	f = 1 MHz	0.3	1.5	3	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 2 $\Omega$		10	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ 8 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		22	33	- ns
Fall Time <sup>c</sup>	t <sub>f</sub>			7	14	
Drain-Source Body Diode Ratings a	nd Characteri	stics (T <sub>C</sub> = 25 °C) <sup>b</sup>				
Continuous Current	۱ <sub>S</sub>				50	٨
Pulsed Current	I <sub>SM</sub>				60	A
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 8 A, V <sub>GS</sub> = 0 V		0.75	1.2	V
Reverse Recovery Time	t <sub>rr</sub>			55	83	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 8 A, dI/dt = 100 A/μs		4.1	6.2	А
Reverse Recovery Charge	Q <sub>rr</sub>			107	161	nC

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

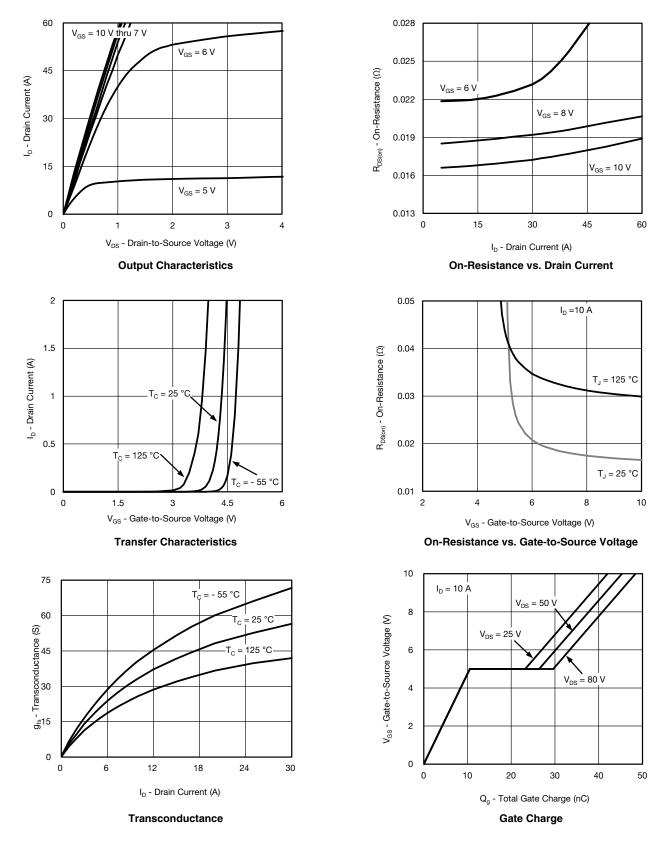
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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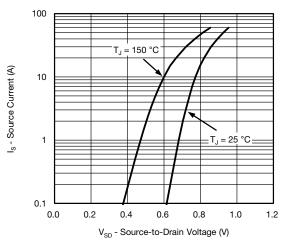
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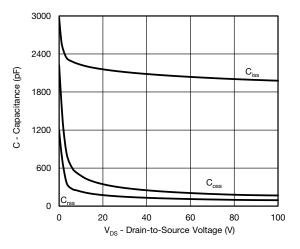


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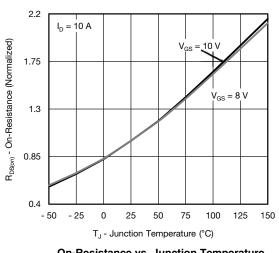
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



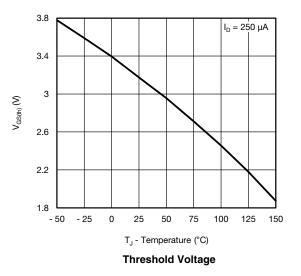
Source-Drain Diode Forward Voltage

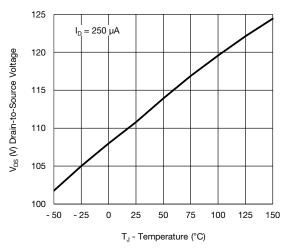




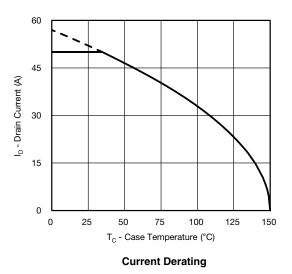


**On-Resistance vs. Junction Temperature** 





Drain Source Breakdown vs. Junction Temperature



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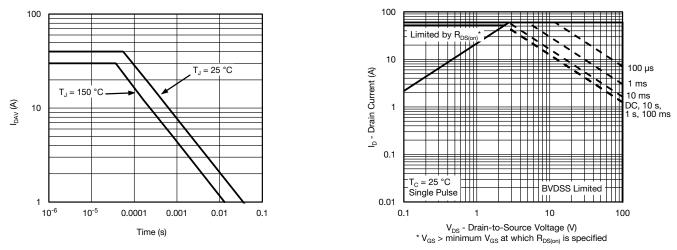
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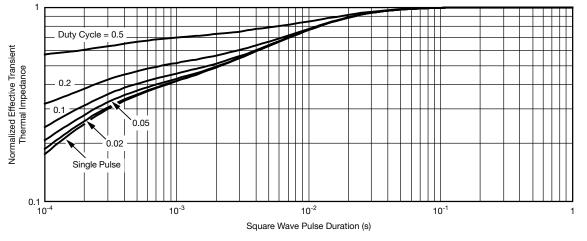
### Vishay Siliconix

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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### **TO-220AB**



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØР	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
	0413-Rev. P,		0.102	0.118

Note

 $^{\star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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